

AMENDMENTS

In The Claims:

This list of claims will replace all prior versions and listings of claims in the application. Please amend the claims as set forth below.

1. **(Currently amended)** A self-refresh device, comprising:

a command decoder for ~~outputting a mode register set signal, a self-refresh signal and a refresh flag signal~~ by decoding an externally inputted refresh command to output a mode register set signal, a self-refresh signal and a refresh flag signal;

a refresh counter for ~~outputting a refresh request signal~~ by performing a counting operation corresponding to a refresh cycle in response to the refresh flag signal to output a refresh request signal;

an internal address counter for counting and generating an internal address in response to the refresh flag signal and the refresh request signal;

a partial array self-refresh decoder for generating a plurality of control signals for performing a partial array self-refresh operation in response to the mode register set signal, the self-refresh signal, and the internal address; and

a row address strobe generator for ~~controlling~~ generating a row active signal for selectively activating a quarter or a half of a plurality of the one or more banks and a quarter or a half of the activated banks ~~or a certain region in a selected single bank~~ depending on states of the plurality of control signals when a refresh operation signal is activated.

2. **(Previously presented)** The device according to claim 1, further comprising:

a row pre-decoder for outputting an external address as a row address in a normal mode, and outputting the internal address as the row address in a refresh mode.

3-5. **(Canceled)**

6. **(Currently amended)** The device according to claim 1, wherein the partial array self-refresh decoder comprises:

an extended mode register set decoder for outputting a register set control signal by decoding a bank selection address in response to the mode register set signal;

a plurality of address latches each for outputting register set ~~address-bit~~ addresses by latching an external address, in response to the register set control signal, ~~and~~ the self-refresh signal ~~[[when]], and~~ the mode register set signal ~~is applied~~; and

a partial array self-refresh controller for selectively activating the plurality of control signals by decoding the plurality of register set addresses depending on the internal address.

7. **(Previously presented)** The device according to claim 6, wherein the register set control signal is activated when the mode register set signal is activated, a most significant bit address of the bank selection address is high, and a second most significant bit of the bank selection address is low.

8. **(Original)** The device according to claim 7, wherein the extended mode register set decoder comprises:

a first inverter for inverting the second most significant bit of the bank selection address;

a first NAND gate for NANDing the most significant bit of the bank selection address and an output signal of the first inverter;

a second inverter for inverting an output signal of the first NAND gate; and

a second NAND gate for outputting the register set control signal by NANDing the mode register set signal and an output signal of the second inverter.

9. **(Previously presented)** The device according to claim 6, wherein each of the plurality of address latches comprises:

a first switch for selectively outputting one of the plurality of external addresses in response to the mode register set signal;

a first latch for latching an output signal of the first switch;

a second switch for selectively outputting an output signal of the first latch in response to the register set control signal;

a second latch for latching an output signal of the second switch; and

a first logic unit for outputting an output signal of the second latch as one of the plurality of register set addresses in activation of the self-refresh signal.

10. **(Currently Amended)** The device according to claim 9, wherein the first latch and the second latch, respectively, comprise a third inverter and a fourth inverter [[where]] wherein each output signal is ~~feedback~~ fed back as an input signal.

11. **(Currently Amended)** The device according to claim 9, wherein the first logic unit comprises:

a third NAND gate for NANDing the self-refresh signal and an output signal of the second latch; and

a ~~seventh~~ fifth inverter for inverting an output signal of the third NAND gate.

12. **(Previously presented)** The device according to claim 6, wherein the partial array self-refresh controller outputs the plurality of control signals by decoding the plurality of register set addresses and the plurality of inverted register set addresses.

13. **(Currently amended)** The device according to claim 12, wherein one of the plurality of control ~~signal~~ signals is outputted when at least one of the most and the second most significant bits of the bank selection address is high.

14. **(Previously presented)** The device according to claim 1, wherein the row address strobe generator generates the row active signal depending on a bank selection address and a normal operation signal in a normal mode, and generates the row active signal depending on the plurality of control signals and the refresh operation signal in a refresh mode.

15. **(Previously presented)** The device according to claim 14, wherein the row address strobe generator comprises:

a first switching means for being selectively turned on in response to the normal operation signal and the refresh operation signal;

a second switching means for being selectively turned on depending on the bank selection address and the normal operation signal; and

a third switching means for being selectively turned on depending on the plurality of control signals and the refresh operation signal.

16. **(Previously presented)** The device according to claim 15, wherein the first switching means comprises a first PMOS transistor and a second PMOS transistor connected in series between a power source terminal and the second switching means, wherein the first PMOS transistor and the second PMOS transistor having each gate to receive the normal operation signal and the refresh operation signal, respectively.

17. **(Previously presented)** The device according to claim 15, wherein the second switching means comprises a first NMOS transistor and a second NMOS transistor connected between the first switching means and a ground terminal, wherein the first NMOS transistor and the second NMOS transistor having gates to receive the normal operation signal and the bank selection address, respectively.

18. **(Previously presented)** The device according to claim 15, wherein the third switching means comprises a third NMOS transistor and a fourth NMOS transistor connected between the first switching means and a ground terminal, wherein the third NMOS transistor and the fourth NMOS transistor having gates to receive the refresh operation signal and the plurality of control signals.

19. **(Original)** The device according to claim 1, wherein the row address strobe generator is comprised to have the same number of the banks.

20. **(Canceled)**

21. **(Previously presented)** The device according to claim 6, wherein the extended mode register set decoder sets up a code for performing a self-refresh operation on a cell array corresponding to a half of one bank when a partial array self-refresh operation is in a half of bank mode, and for performing a self-refresh operation on a cell array corresponding to a quarter of one bank when a partial array self-refresh operation is in a quarter of bank mode.

22. **(Previously presented)** The device according to claim 21, wherein when the partial array self-refresh operation is in a half of bank mode, the partial array self-refresh decoder activates a number of control signals corresponding to a quarter of the plurality of control signals until a most significant bit of address becomes high.

23. **(Previously presented)** The device according to claim 21, wherein when the partial array self-refresh operation is in a quarter of bank mode, the partial array self-refresh decoder activates a number of control signals corresponding to a quarter of the plurality of control signals until at least one of two most significant bits of address becomes high.